

**Silicon PNP Power Transistor**

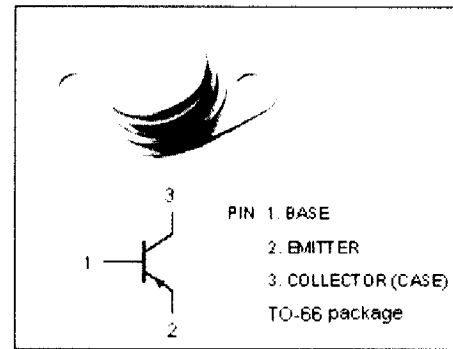
**2SA765**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -80V(\text{Min})$
- Low Collector Saturation Voltage-  
 :  $V_{CE(sat)} = 1.5V(\text{Max.}) @ I_C = 4A$
- Complement to Type 2SC1445

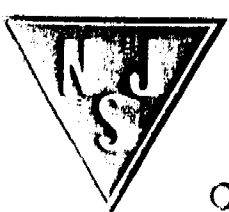
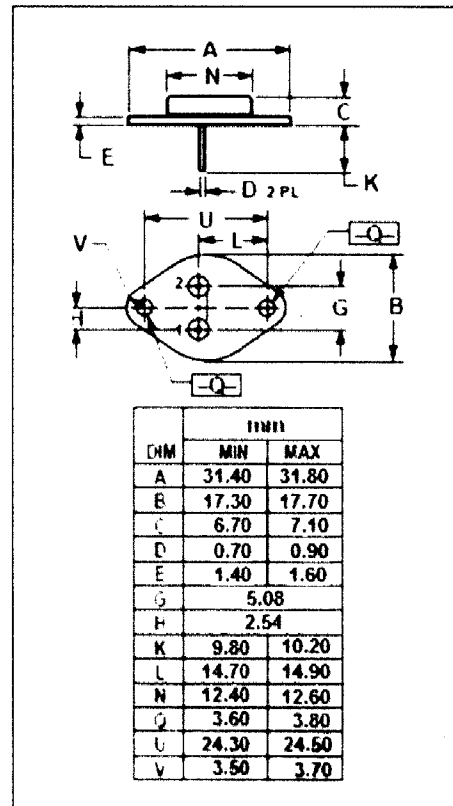
**APPLICATIONS**

- Designed for general purpose power amplifier applications



**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-80	V
$V_{CEO}$	Collector-Emitter Voltage	-80	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-6	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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# 2SA765

## ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-80			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1\text{mA}; I_E = 0$	-80			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -4\text{A}; I_B = -0.4\text{A}$			-1.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -4\text{A}; I_B = -0.4\text{A}$			-2.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -80\text{V}; I_E = 0$			-10	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -6\text{V}; I_C = 0$			-10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	50			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -12\text{V}$		10		MHz